

# TM07G04S

## N+P-Channel Enhancement Mode Mosfet

<p><b>General Description</b></p> <ul style="list-style-type: none"> <li>• Low <math>R_{DS(ON)}</math></li> <li>• RoHS and Halogen-Free Compliant</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>• Load switch</li> <li>• PWM</li> </ul>	<p><b>General Features</b></p> <p><b>N Channel</b>  <math>V_{DS} = 40V, I_D = 7.3A</math>  <math>R_{DS(ON)} = 26m\Omega (typ.) @ V_{GS} = 10V</math></p> <p><b>P Channel</b>  <math>V_{DS} = -40V, I_D = -6.1A</math>  <math>R_{DS(ON)} = 56m\Omega (typ.) @ V_{GS} = -10V</math></p> <p>100% UIS Tested          100% <math>R_g</math> Tested</p>
------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------	------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------



S:SOP-8L

Marking: 7004

**Absolute Maximum Ratings** ( $T_A = 25^\circ C$  unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
$V_{DS}$	Drain-Source Voltage	40	-40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	$\pm 20$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	7.3	-6.1	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	5.2	-4.2	A
$I_{DM}$	Pulsed Drain Current	25	-22	A
EAS	Single Pulse Avalanche Energy	16.2	39	mJ
$I_{AS}$	Avalanche Current	6.8	-6.5	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	1.67	1.67	W
$T_{STG}$	Storage Temperature Range	-55 to 175	-55 to 175	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 175	-55 to 175	$^\circ C$

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	---	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	62.5	$^\circ C/W$



# TM07G04S

## N+P-Channel Enhancement Mode Mosfet

### N-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	44	---	V
ΔBVDSS/ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.034	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =5A	---	26	35	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	---	36	45	
VGS(th)	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.6	2.0	V
ΔVGS(th)	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.56	---	mV/°C
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =32V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =5A	---	14	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	2.6	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =20V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	---	5.5	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	1.25	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	2.5	---	
Td(on)	Turn-On Delay Time	V <sub>DD</sub> =20V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =1A	---	8.9	---	ns
T <sub>r</sub>	Rise Time		---	2.2	---	
Td(off)	Turn-Off Delay Time		---	41	---	
T <sub>f</sub>	Fall Time		---	2.7	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	593	---	pF
C <sub>oss</sub>	Output Capacitance		---	76	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	56	---	
I <sub>s</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	7.3	A
ISM	Pulsed Source Current		---	---	23	A
VSD	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V



# TM07G04S

## N+P-Channel Enhancement Mode Mosfet

### P-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-40	-44	---	V
ΔBVDSS/ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.018	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A	---	56	66	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A	---	67	79	
VGS(th)	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.0	-1.75	-2.5	V
ΔVGS(th)	V <sub>GS(th)</sub> Temperature Coefficient		---	2.5	---	mV/°C
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =-40V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-40V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	-5	
IGSS	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-3A	---	5.8	---	S
Qg	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-32V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	---	6.4	---	nC
Qgs	Gate-Source Charge		---	2.1	---	
Qgd	Gate-Drain Charge		---	2.5	---	
Td(on)	Turn-On Delay Time	V <sub>DD</sub> =-20V, V <sub>GS</sub> =-4.5V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =-3A	---	4.2	---	ns
T <sub>r</sub>	Rise Time		---	23	---	
Td(off)	Turn-Off Delay Time		---	26.8	---	
T <sub>f</sub>	Fall Time		---	20.6	---	
Ciss	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	---	620	---	pF
Coss	Output Capacitance		---	65	---	
Crss	Reverse Transfer Capacitance		---	53	---	
IS	Continuous Source Current <sup>1,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-6.1	A
ISM	Pulsed Source Current <sup>2,4</sup>		---	---	-16.1	A
VSD	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1	V

**Note :**

- 1、 The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width ≅ 300us , duty cycle ≅ 2%
- 3、 The power dissipation is limited by 150°C junction temperature
- 4、 The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.



TM07G04S

N+P-Channel Enhancement Mode Mosfet

N-Channel Typical Characteristics

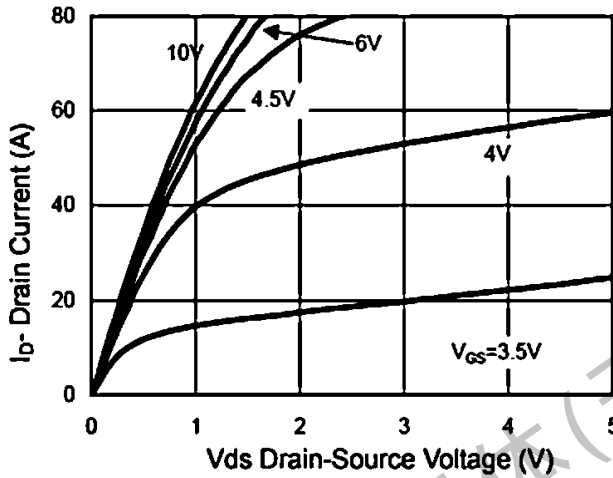


Figure 1 Output Characteristics

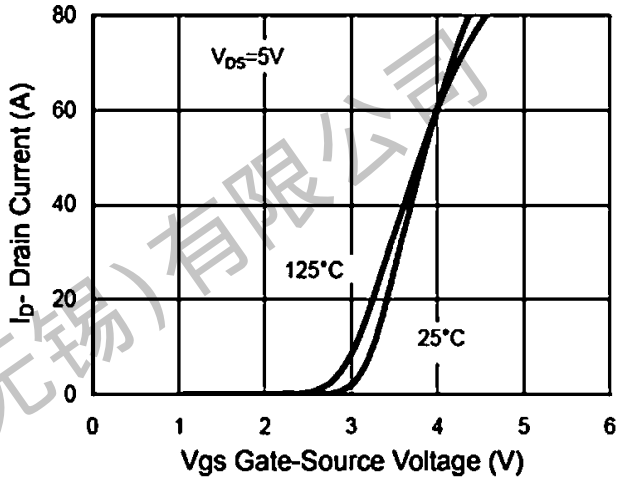


Figure 2 Transfer Characteristics

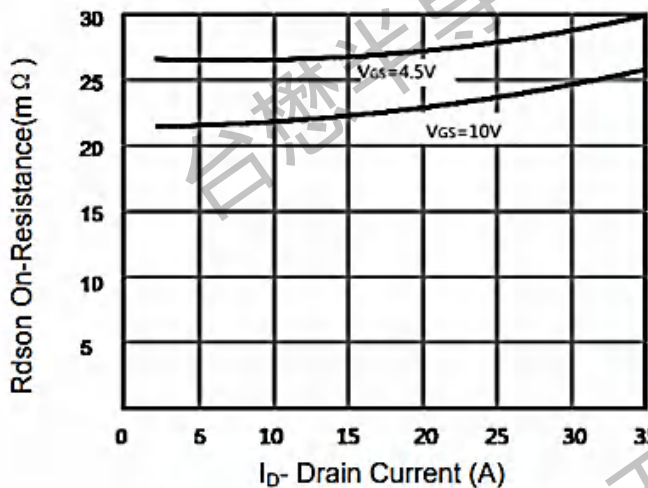


Figure 3 Rdson- Drain Current

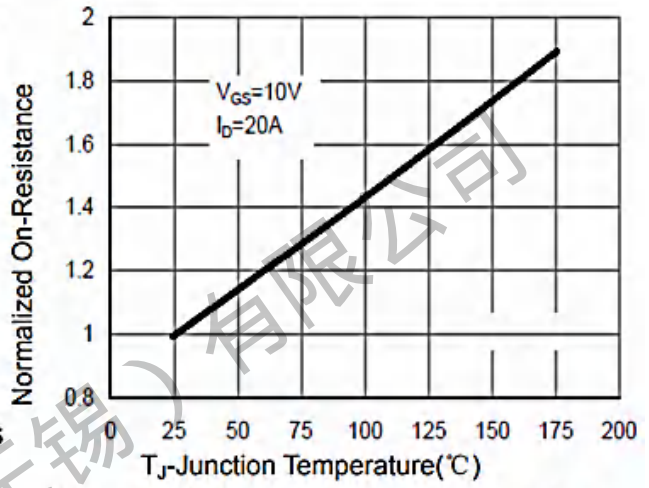


Figure 4 Rdson-Junction Temperature

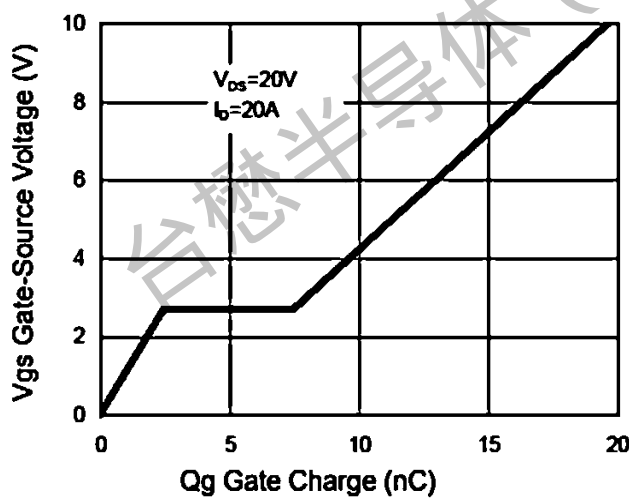


Figure 5 Gate Charge

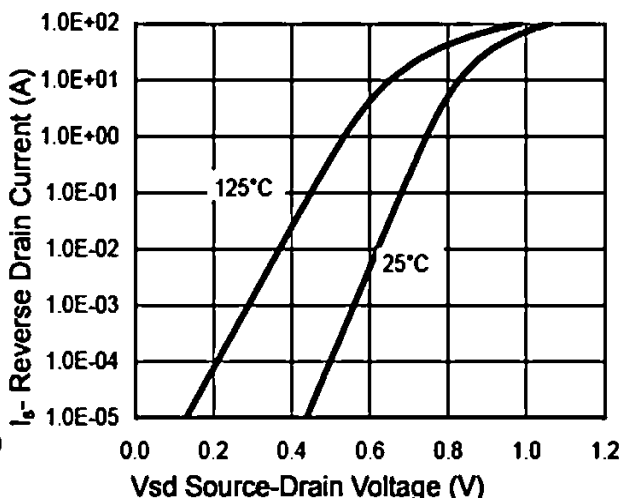


Figure 6 Source- Drain Diode Forward



TM07G04S

N+P-Channel Enhancement Mode Mosfet

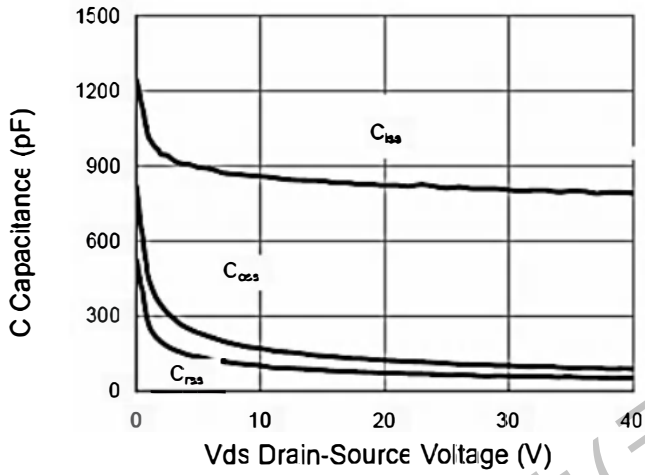


Figure 7 Capacitance vs Vds

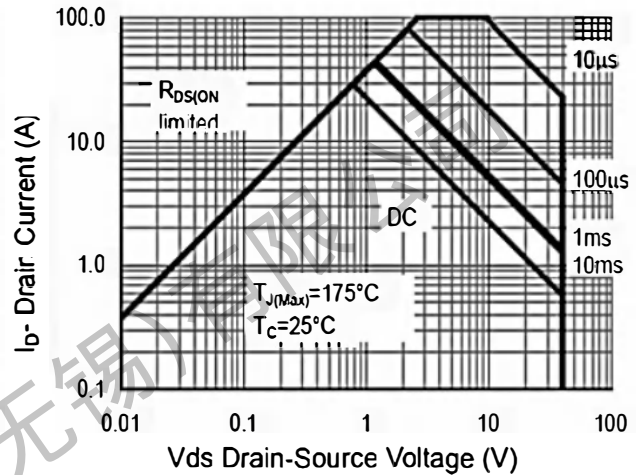


Figure 8 Safe Operation Area

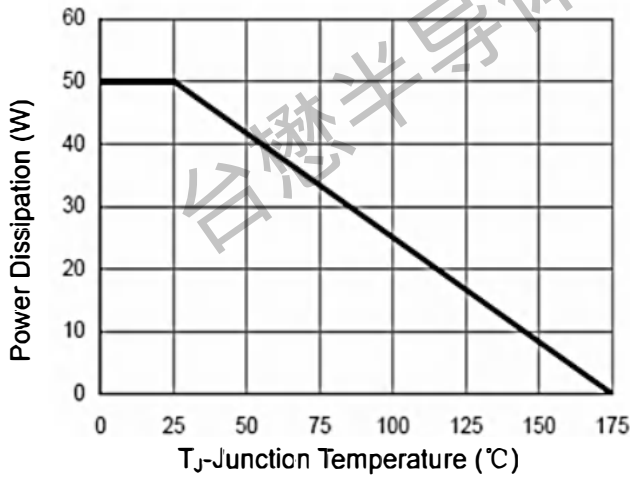


Figure 9 Power De-rating

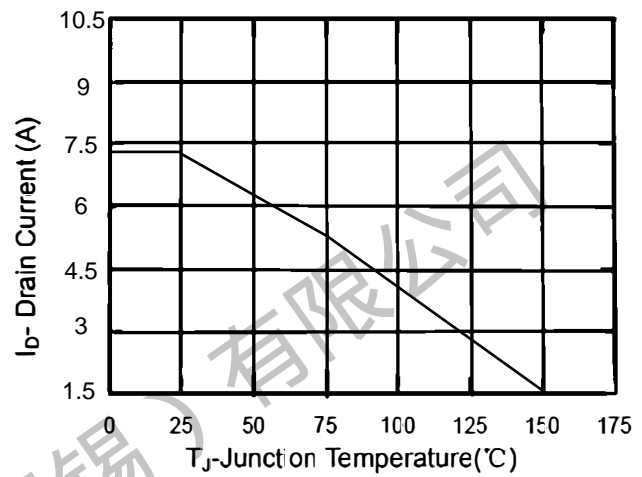


Figure 10 Id Current De-rating

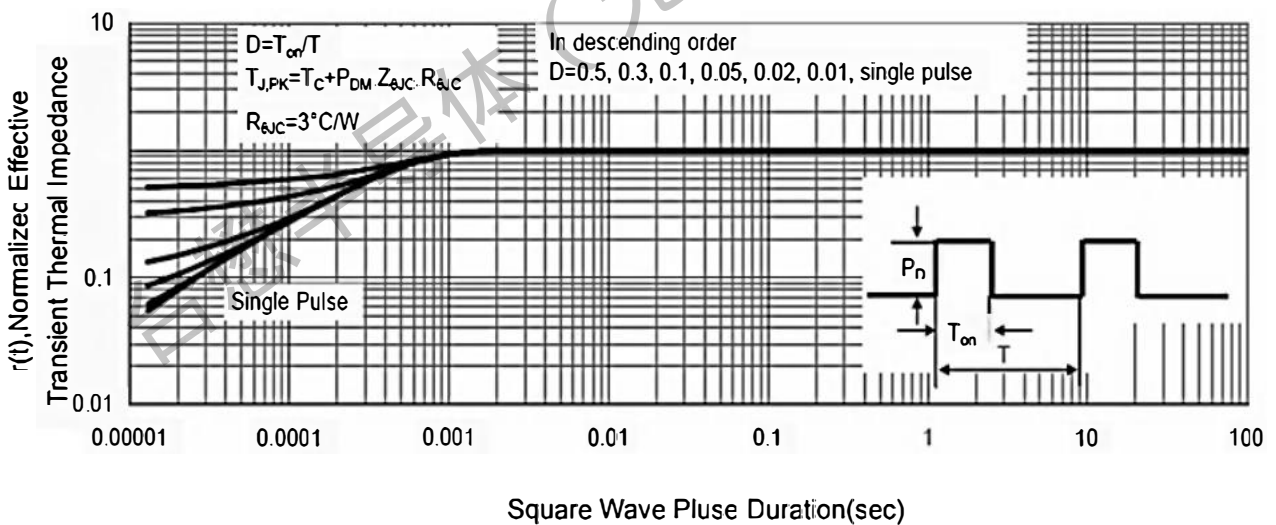


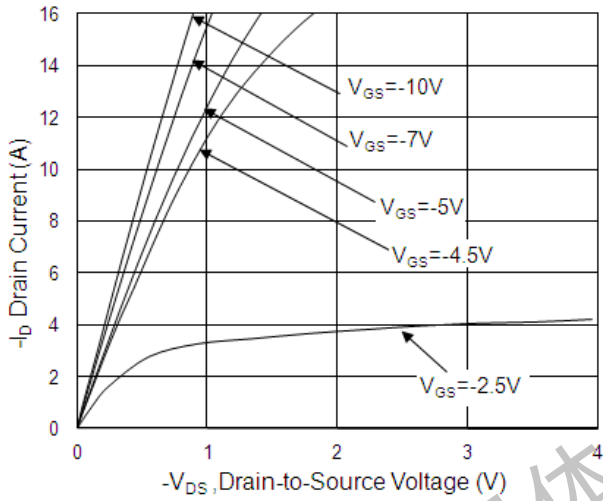
Figure 11 Normalized Maximum Transient Thermal Impedance



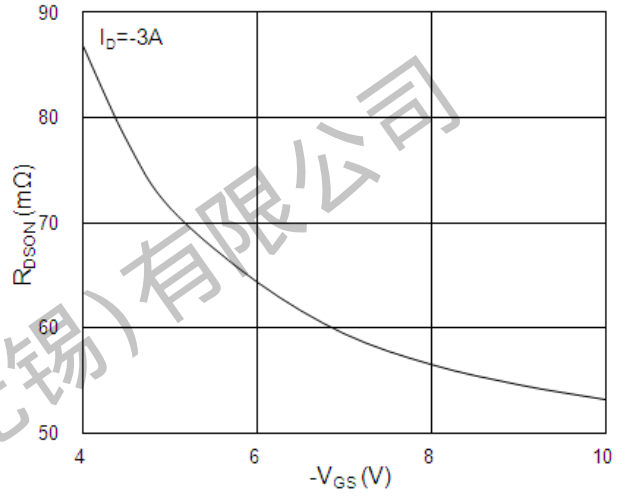
**TM07G04S**

**N+P-Channel Enhancement Mode Mosfet**

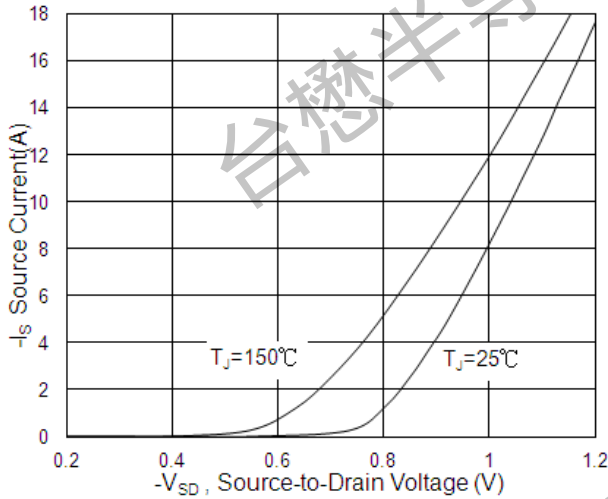
**P-Typical Characteristics**



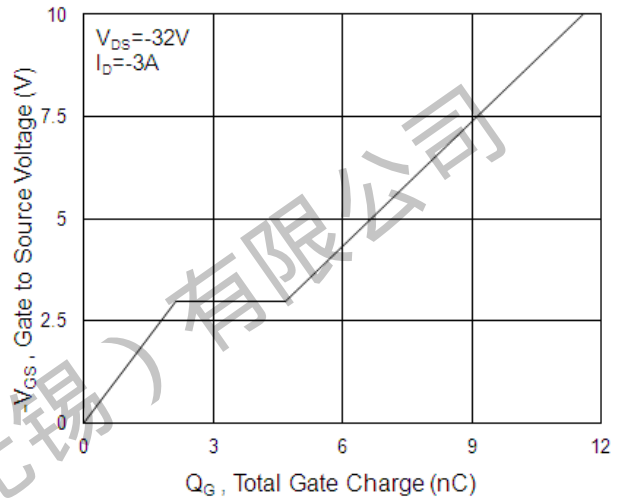
**Fig.1 Typical Output Characteristics**



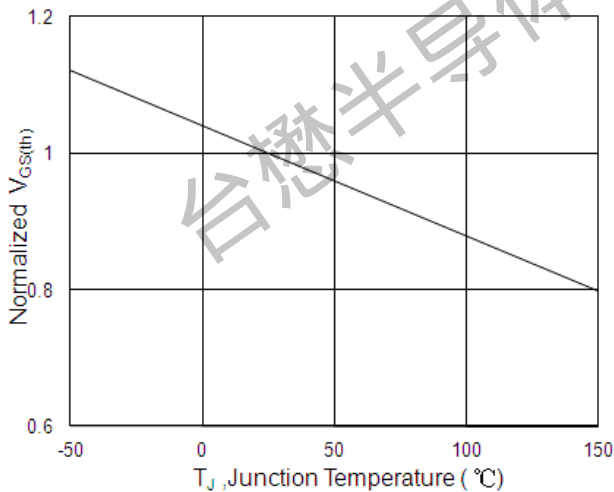
**Fig.2 On-Resistance vs. G-S Voltage**



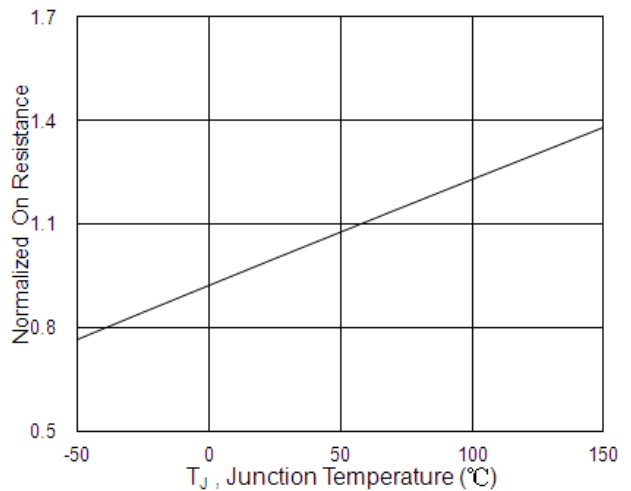
**Fig.3 Forward Characteristics Of Reverse**



**Fig.4 Gate-Charge Characteristics**



**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



# TM07G04S

## N+P-Channel Enhancement Mode Mosfet

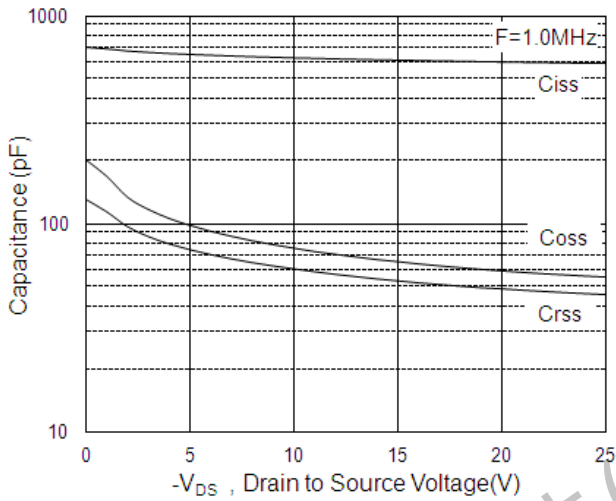


Fig.7 Capacitance

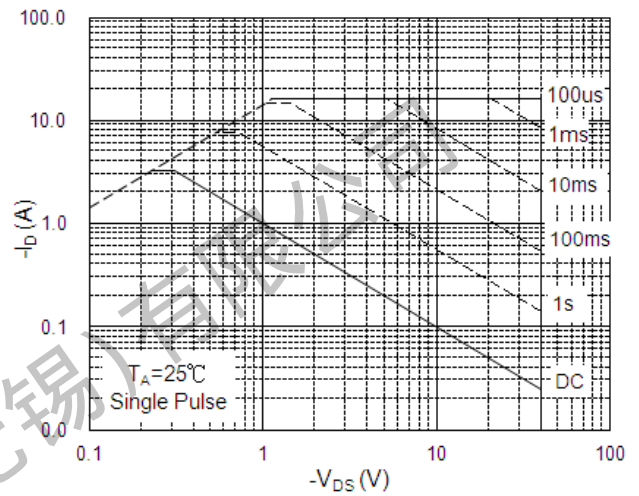


Fig.8 Safe Operating Area

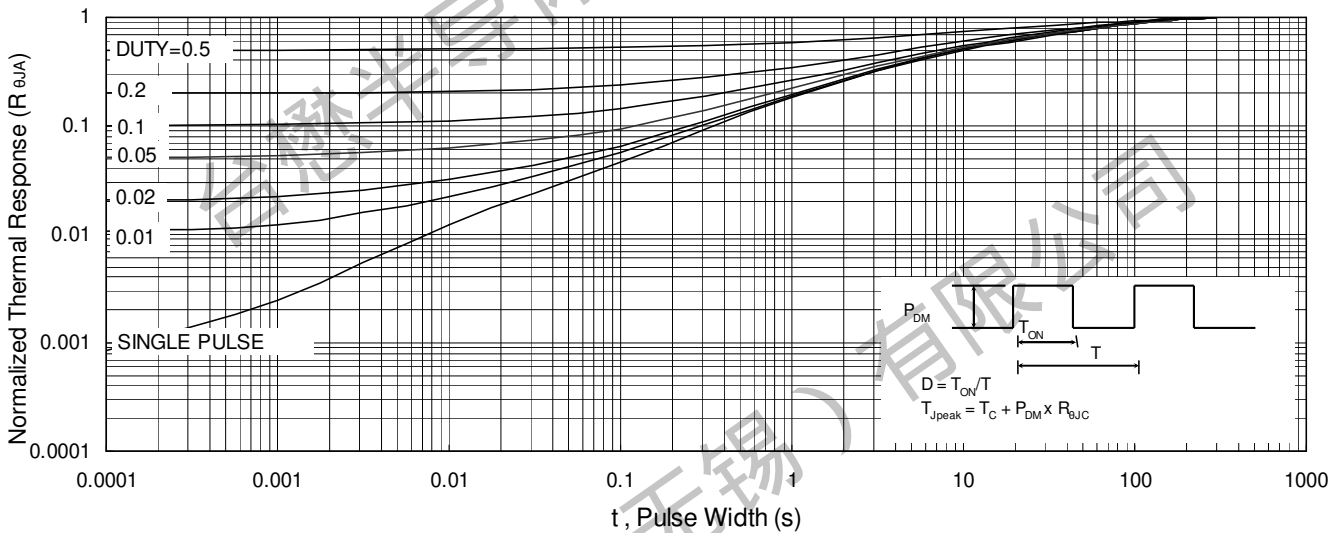


Fig.9 Normalized Maximum Transient Thermal Impedance

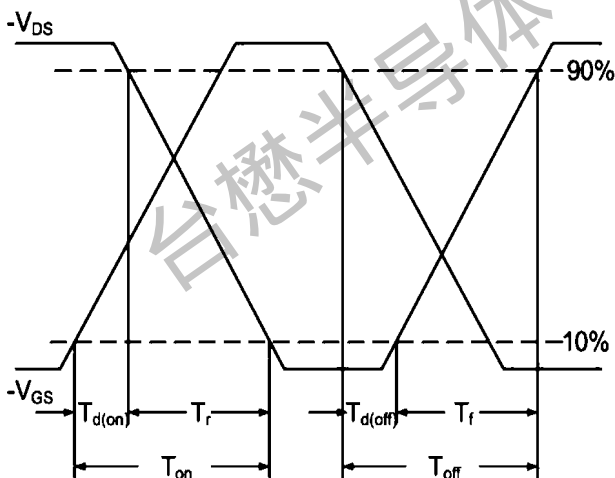


Fig.10 Switching Time Waveform

Data and specifications subject to change without notice.

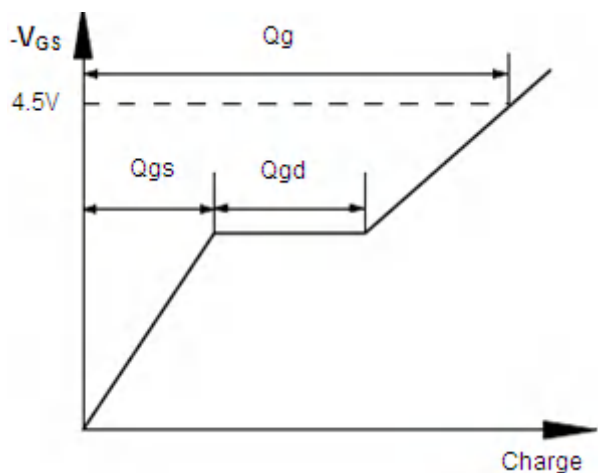


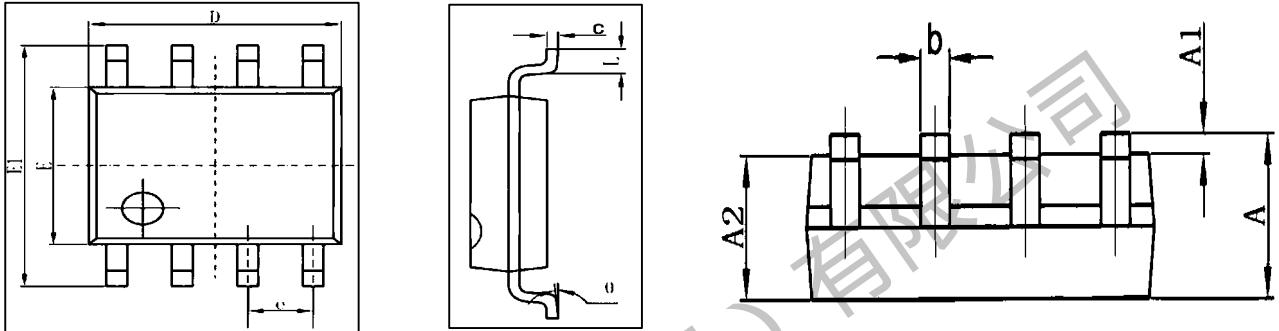
Fig.11 Gate Charge Waveform



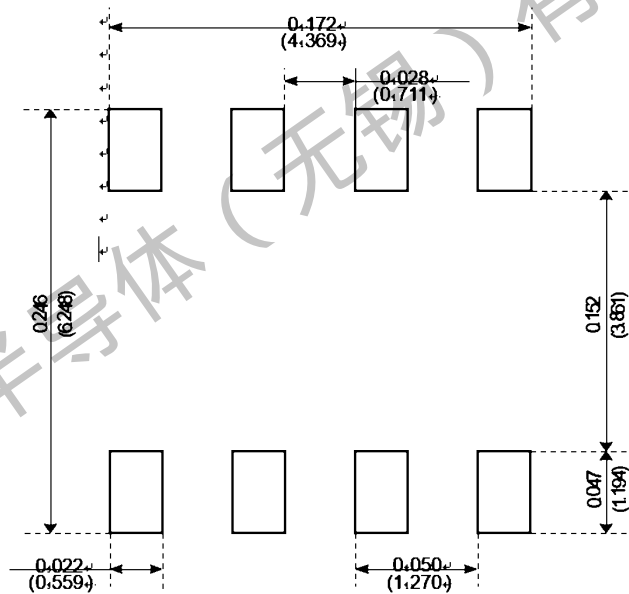
**TM07G04S**

**N+P-Channel Enhancement Mode Mosfet**

**Package Mechanical Data:SOP-8L**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

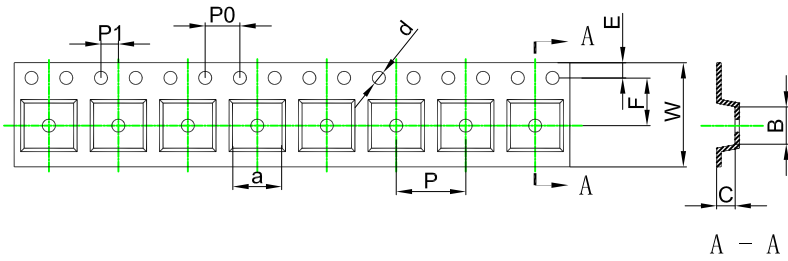


Recommended Minimum Pads

**TM07G04S**

**N+P-Channel Enhancement Mode Mosfet**

**SOP-8L Embossed Carrier Tape**



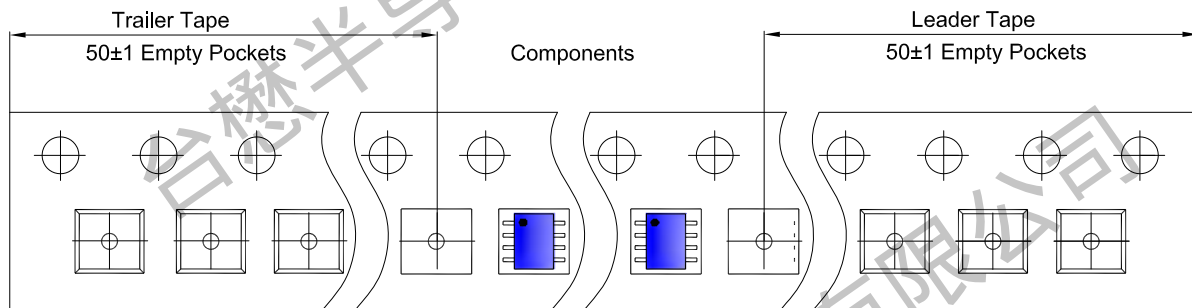
**Packaging Description:**

SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

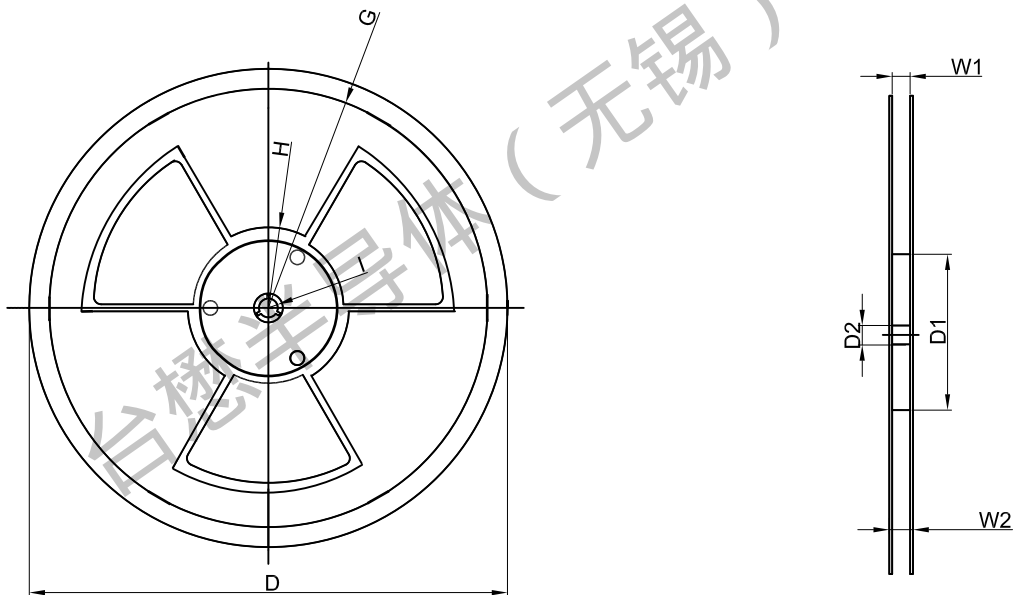
**ALL DIM IN mm**

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
SOP-8L	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

**SOP-8L Tape Leader and Trailer**



**SOP-8L Reel**



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13"Dia	Ø330.00	100.00	13.00	R135.00	R55.00	R6.50	12.00	14.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3,000 pcs	13 inch	6,000 pcs	370×355×52	48,000 pcs	400×360×368	

### Important Notices and Disclaimers

- Tritech-MOS Technology Corp. reserves the right to change this document, its products, and specifications at any time without prior notice.
- Before final design, purchase, or use, customers should obtain and confirm the latest product information and specifications.
- Tritech-MOS Technology Corp. makes no warranties, representations or warranties regarding the suitability of its products for any specific purpose, and Tritech-MOS Technology Corp. does not assume any responsibility for application assistance or customer product design.
- Tritech-MOS Technology Corp. does not guarantee or assume any responsibility for the purchase or use of any unexpected or unauthorized products.
- Any intellectual property rights of Tritech-MOS Technology Corp. are not licensed through implicate or other means.
- Products of Tritech-MOS Technology Corp. are not included as critical components in life support equipment or systems without explicit written approval from Tritech-MOS Technology Corp.

Revision history:

Date	Rev	Description	Page
2023.05.19	23.05	Original	